

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A high-frequency circuit board unit comprising:
a circuit board including a first surface and a second surface;
a ground electrode provided on said first surface of said circuit board;
a terminal electrode provided on said first surface of said circuit board; and
a semiconductor device mounted on said second surface of said circuit board,
said semiconductor device including a high-frequency signal terminal for sending and
receiving a high-frequency signal to and from said terminal electrode of said circuit board,
and a non-high-frequency signal terminal located on said semiconductor device ~~and~~,
wherein said non-high-frequency signal terminal is not connected to any
terminal electrode on said first surface of said circuit board so as to be isolated from receipt
of a surge voltage, and
wherein at least one of said terminal electrode and said high-frequency signal
terminal of said semiconductor device is connected to said ground electrode for conducting
direct current.

2. (Original) A high-frequency circuit board unit according to claim 1, further
comprising a passive impedance circuit device mounted on said circuit board and connected
between said high-frequency signal terminal and said terminal electrode,
wherein one of said high-frequency signal terminal and said terminal electrode is
connected to said ground electrode for conducting direct current via said passive
impedance circuit device.

3. (Original) A high-frequency circuit board unit according to claim 1, further comprising a passive impedance circuit device mounted on said circuit board and connected between said high-frequency signal terminal and said terminal electrode,

wherein both said high-frequency signal terminal and said terminal electrode are connected to said ground electrode for conducting direct current via said passive impedance circuit device.

4. (Original) A high-frequency circuit board unit according to one of claims 2 and 3, wherein said passive impedance circuit device is formed on a dielectric substrate having a dielectric constant higher than that of both said circuit board and said semiconductor device.

5. (Original) A high-frequency circuit board unit according to one of claims 2 and 3, wherein said semiconductor device is bump-mounted on said circuit board.

6. (Original) A high-frequency circuit board unit according to any one of claims 1 to 3, further comprising an additional terminal other than said high-frequency signal terminal on said semiconductor device, and an electrostatic protecting diode connected to said additional terminal.

7. (Previously Presented) A high-frequency module comprising said high-frequency circuit board unit set forth in any one of claims 1 to 3, further comprising a cover mounted on said second surface of said circuit board.

8. (Original) An electronic apparatus comprising said high-frequency module set forth in claim 7.

9. (Original) An electronic apparatus comprising said high-frequency circuit board unit set forth in any one of claims 1 to 3.

10. (Currently Amended) A manufacturing method for a high-frequency circuit board unit, the manufacturing method comprising:

mounting a passive impedance circuit device on a first surface of a circuit board, said circuit board including a ground electrode and a terminal electrode provided on a second surface thereof, wherein at least one terminal of said passive impedance circuit device is connected to said ground electrode and said terminal electrode for conducting direct current; and

mounting a semiconductor device including a high-frequency signal terminal and a non-high-frequency signal terminal on said first surface of said circuit board in such a manner that said high-frequency signal terminal is connected to a second terminal of said passive impedance circuit device, and said non-high-frequency signal terminal is not connected to any terminal electrode on said second surface of said circuit board so as to be is isolated from receipt of a surge voltage.

11. (Original) A manufacturing method for a high-frequency circuit board unit according to claim 10, wherein said passive impedance circuit device and said semiconductor device are bump-mounted on said circuit board.

12. (Original) A manufacturing method according to claim 10, wherein said at least one terminal of said passive impedance circuit device is connected to said ground electrode after said semiconductor device is mounted on said circuit board.

13. (Previously Presented) A manufacturing method according to claim 12, wherein said at least one terminal of said passive impedance circuit device is connected to said ground electrode before said high-frequency signal terminal is connected to said second terminal of said passive impedance circuit device.